U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Serial No.
	M-11822 US	09/925,102
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Jack H. Yuan et al.	
	Filing Date	Group
	August 8, 2001	2185

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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Sheet 1 of 1

U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.257US0	09/925,102
	Applicant(s)	
(Use several sheets if necessary)	Jack H. Yuan et al.	
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